



# FDS5351

## N-Channel PowerTrench® MOSFET

### 60V, 6.1A, 35mΩ

#### Features

- Max  $r_{DS(on)}$  = 35mΩ at  $V_{GS} = 10V, I_D = 6.1A$
- Max  $r_{DS(on)}$  = 42mΩ at  $V_{GS} = 4.5V, I_D = 5.5A$
- High performance trench technology for extremely low  $r_{DS(on)}$
- 100% UIL Tested
- RoHS Compliant

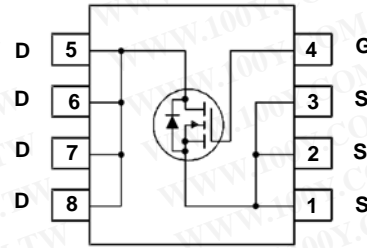
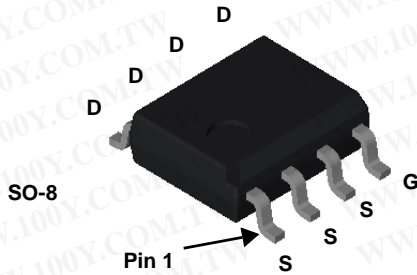


#### General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

#### Application

- Inverter Switch
- Synchronous Rectifier
- Load Switch



#### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
$V_{DS}$	Drain to Source Voltage	60	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous	6.1	A
	-Pulsed	30	
$E_{AS}$	Single Pulse Avalanche Energy (Note 3)	73	mJ
$P_D$	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	5	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1b)	2.5	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

#### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	25	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

#### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS5351	FDS5351	SO-8	13"	12mm	2500units

### Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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#### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		55		mV/°C
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			$\pm 100$	nA

#### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	1.0	2.0	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-6.2		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 6.1\text{A}$		26.5	35.0	m $\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 5.5\text{A}$		32.4	42.0	
		$V_{GS} = 10\text{V}, I_D = 6.1\text{A}, T_J = 125^\circ\text{C}$		44.5	58.8	
$g_{FS}$	Forward Transconductance	$V_{DD} = 5\text{V}, I_D = 6.1\text{A}$		24		S

#### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$		985	1310	pF
$C_{oss}$	Output Capacitance			90	120	pF
$C_{rss}$	Reverse Transfer Capacitance			50	75	pF
$R_g$	Gate Resistance		$f = 1\text{MHz}$		1.7	

#### Switching Characteristics

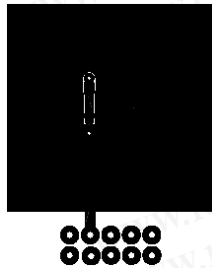
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30\text{V}, I_D = 6.1\text{A},$ $V_{GS} = 10\text{V}, R_{GEN} = 6\Omega$		8	16	ns	
$t_r$	Rise Time			3	10	ns	
$t_{d(off)}$	Turn-Off Delay Time			21	34	ns	
$t_f$	Fall Time			2	10	ns	
$Q_g$	Total Gate Charge		$V_{GS} = 0\text{V to } 10\text{V}$		19	27	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{V to } 4.5\text{V}$	$V_{DD} = 30\text{V},$ $I_D = 6.1\text{A}$		9	13	nC
$Q_{gs}$	Gate to Source Charge				3		nC
$Q_{gd}$	Gate to Drain "Miller" Charge				3.5		nC

#### Drain-Source Diode Characteristics

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 6.1\text{A}$ (Note 2)		0.82	1.3	V
		$V_{GS} = 0\text{V}, I_S = 2.1\text{A}$ (Note 2)		0.76	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = 6.1\text{A}, di/dt = 100\text{A}/\mu\text{s}$		24	38	ns
$Q_{rr}$	Reverse Recovery Charge			15	27	nC

#### NOTES:

1.  $R_{\theta JA}$  is determined with the device mounted on a  $1\text{in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\text{in.}$  board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $50^\circ\text{C}/\text{W}$  when mounted on a  $1\text{in}^2$  pad of 2 oz copper.



b)  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad.

2. Pulse Test: Pulse Width <  $300\mu\text{s}$ , Duty cycle < 2.0%.

3. UIL condition: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 3\text{mH}$ ,  $I_{AS} = 7\text{A}$ ,  $V_{DD} = 60\text{V}$ ,  $V_{GS} = 10\text{V}$ .

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

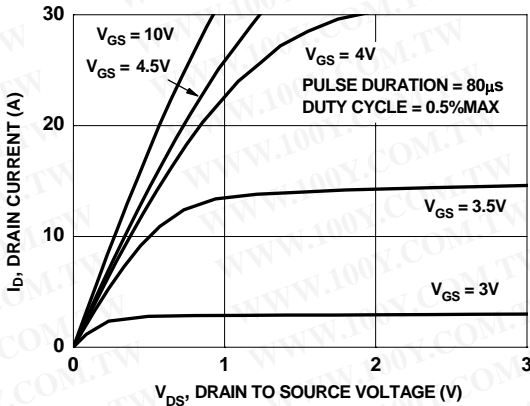


Figure 1. On-Region Characteristics

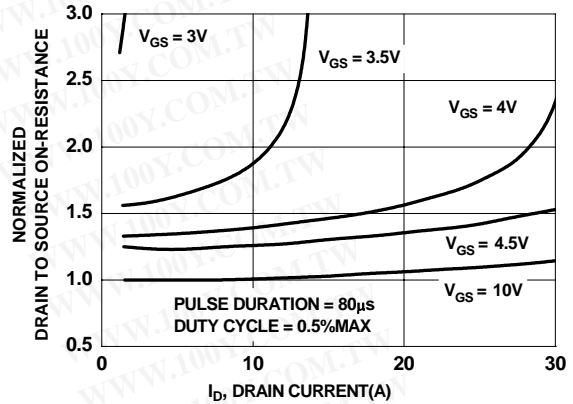


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

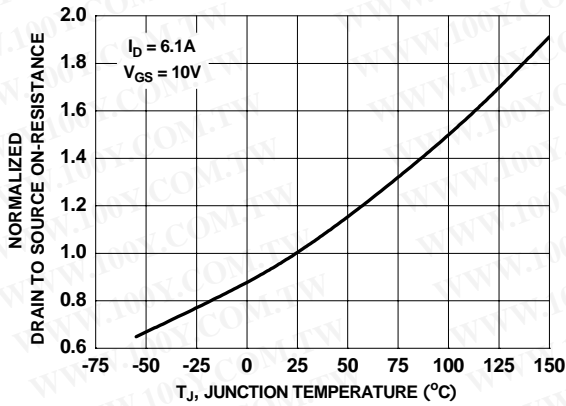


Figure 3. Normalized On-Resistance vs Junction Temperature

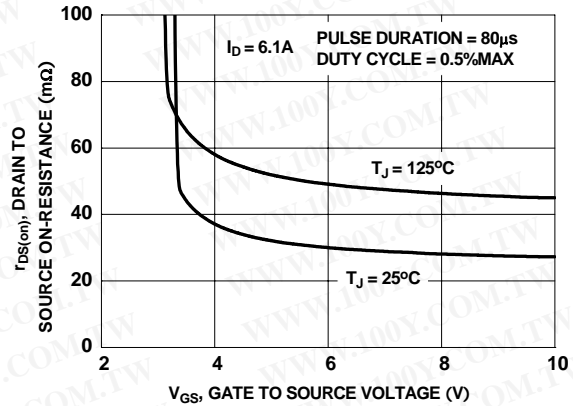


Figure 4. On-Resistance vs Gate to Source Voltage

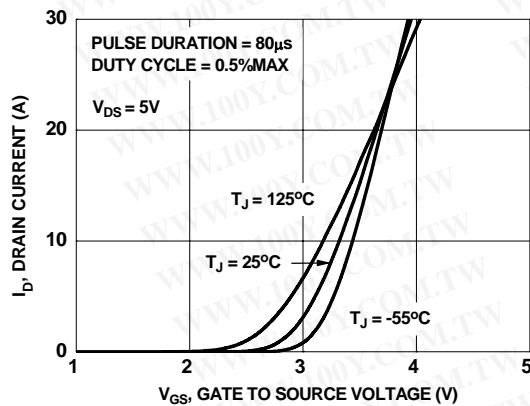


Figure 5. Transfer Characteristics

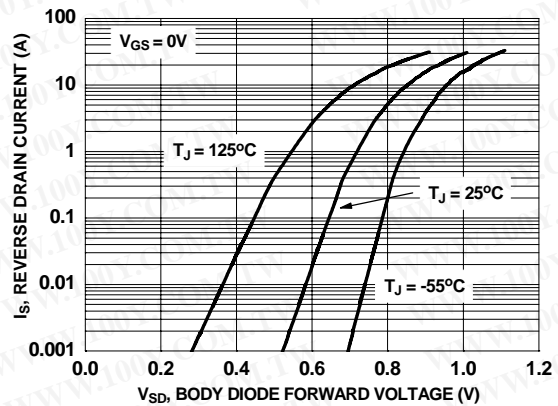
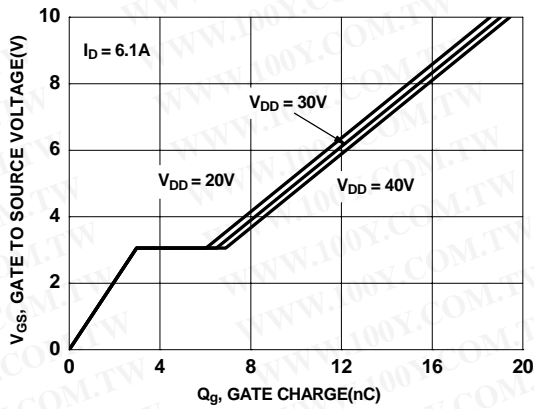
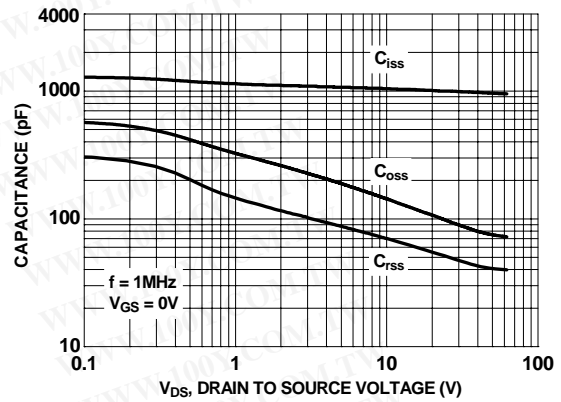


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

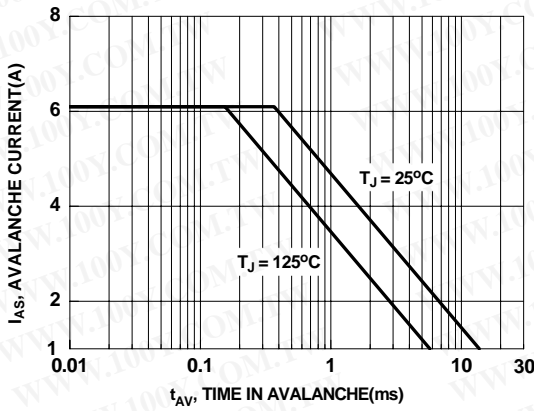
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



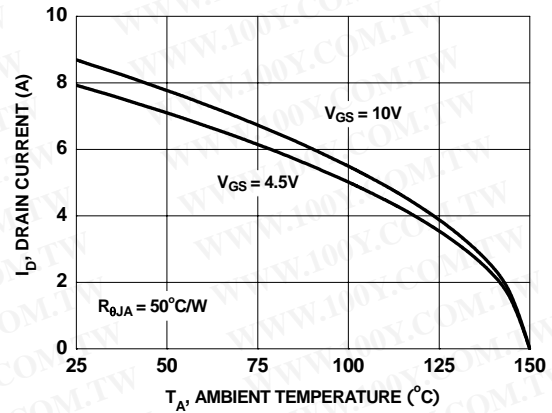
**Figure 7. Gate Charge Characteristics**



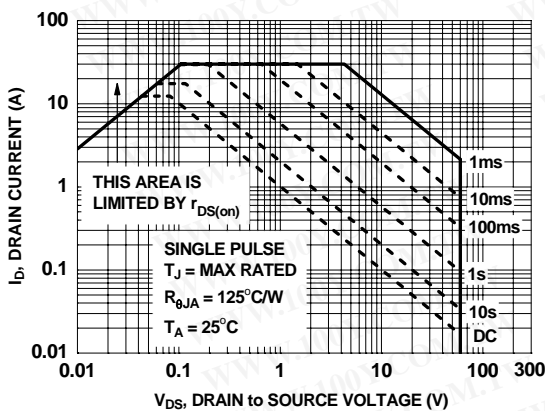
**Figure 8. Capacitance vs Drain to Source Voltage**



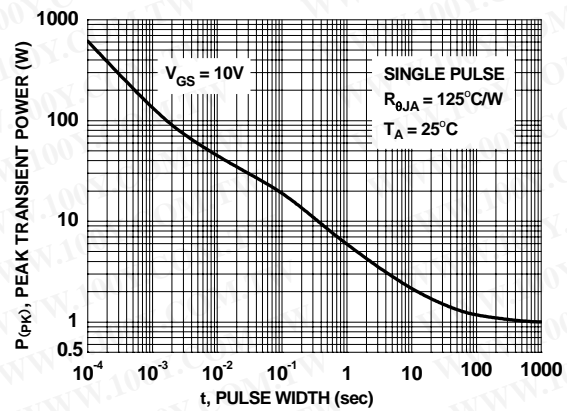
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs Ambient Temperature**

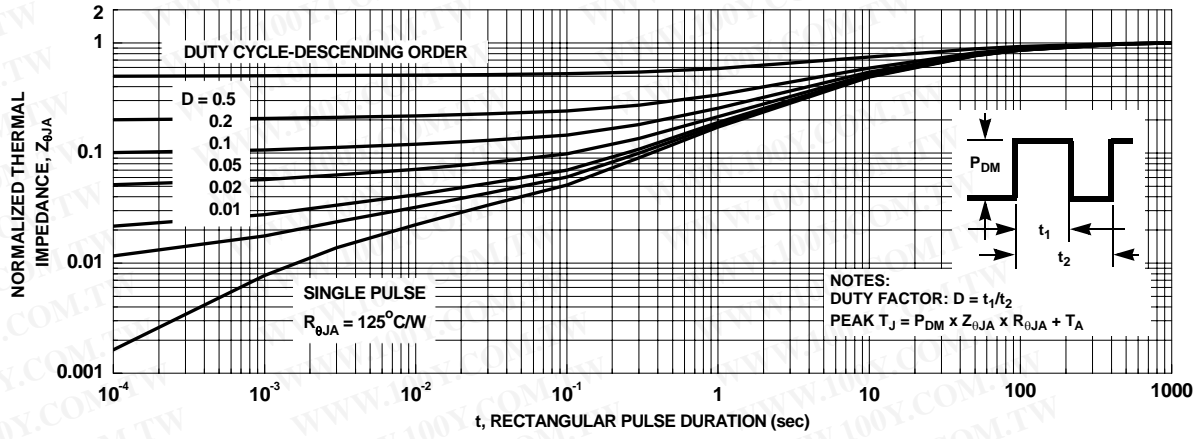


**Figure 11. Forward Bias Safe Operating Area**



**Figure 12. Single Pulse Maximum Power Dissipation**

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted






**Figure 13. Transient Thermal Response Curve**



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